First principle study of WSe_2 and the effect of V doping on the optical and electronic properties

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Table S1. Bandgap e	norgios (calculated b	vusing	GGA-DRE an	d bybrid-HSE06
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Wse ₂	Bandgap obtained by GGA-PBE	Bandgap obtained by hybrid-HSE06
Bulk undoped	0.94 eV (indirect), 1.58 eV (direct)	1.62 eV (indirect) 2.26 eV (direct)
1 ML undoped	1.68 eV (direct)	2.19 eV (direct)
1.4% of V doping	0.93 eV	
2.8% of V doping	0.91 eV	
5.6% of V doping	0.85 eV	
11.2% of V doping	0.80 eV	

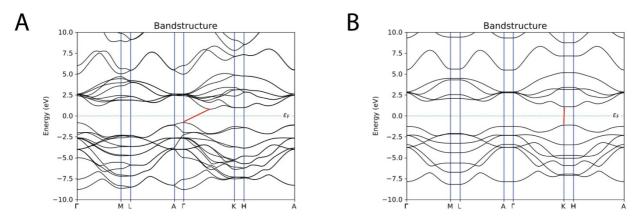


Fig. S1. Band structures of WSe_2 as (A) bulk material and as (B) a single layer calculated by using HybridGGA-HSE06 functional. The Fermi level is depicted as a dashed green line and the band gap as a red line.

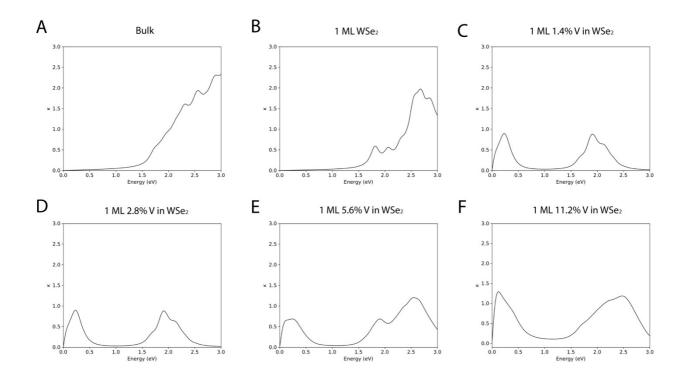


Fig. S2. Extinction coefficient spectra of WSe₂ as a bulk (A) and as 1ML (B). The extinction coefficient of WSe₂ doped with different percentages of V: WSe₂:V 1.4% (C), WSe₂:V 2.8% (D), WSe₂:V 5.6% (E), and WSe₂:V 11.2% (F). The spectra report the extinction coefficient (k) as a function of the energy, between 0 to 3 eV.

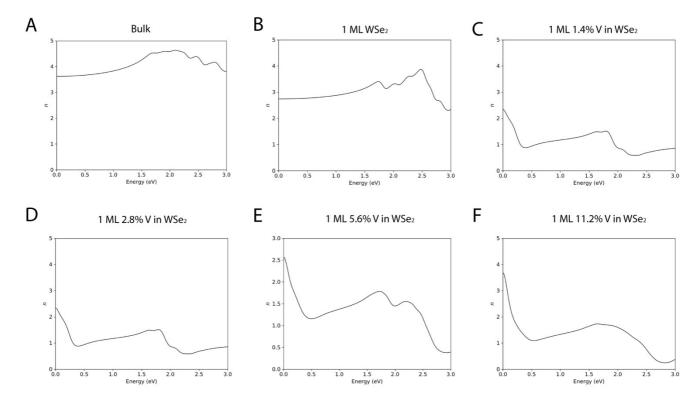


Fig. S3. Refractive index spectra of WSe₂ as a bulk (A) and as 1ML (B). Refractive index of WSe₂ doped with different percentages of V: WSe₂:V 1.4% (C), WSe₂:V 2.8% (D), WSe₂:V 5.6% (E), and WSe₂:V 11.2% (F). The spectra report the refractive index (*n*) as a function of the energy, between 0 to 3 eV.